

# Voltage Protection with Automatic Cell Balance for 2-Series Cell Li-Ion Batteries

Check for Samples: bq29200, bq29209

#### **FEATURES**

- 2-Series Cell Secondary Protection
- Automatic Cell Imbalance Correction with External Enable Control
  - ±30 mV Enable, 0 mV Disable Thresholds Typical
- External Capacitor-Controlled Delay Timer
- External Resistor-Controlled Cell Balance Current
- Low Power Consumption I<sub>CC</sub> < 3 μA Typical (V<sub>CELL</sub>(ALL) < V<sub>PROTECT</sub>)
- Internal Cell Balancing Handles Current up to 15 mA

- External Cell Balancing Mode Supported
- High-Accuracy Overvoltage Protection:
  - ±25 mV with T<sub>A</sub> = 0°C to 60°C
- Fixed Overvoltage Protection Thresholds: 4.30 V, 4.35 V
- Small 8L DRB Package

### **APPLICATIONS**

- 2<sup>nd</sup> Level Protection in Li-lon Battery Packs
  - Netbook Computers
  - Power Tools
  - Portable Equipment and Instrumentation
  - Battery Backup Systems

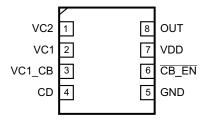
### **DESCRIPTION**

The bq2920x device is a secondary overvoltage protection IC for 2-series cell lithium-ion battery packs that incorporates a high-accuracy precision overvoltage detection circuit and automatic cell imbalance correction.

The voltage of each cell in a 2-series cell battery pack is compared to an internal reference voltage. If either cell reaches an overvoltage condition, the bq2920x device starts a timer that provides a delay proportional to the capacitance on the CD pin. Upon expiration of the internal timer, the OUT pin changes from low to high state.

If enabled, the bq2920x performs automatic cell imbalance correction where the two cells are automatically corrected for voltage imbalance by loading the cell with the higher charge voltage with a small balancing current. When the cells are measured to be equal within nominally 0 mV, the load current is removed. It will be re-applied if the imbalance exceeds nominally 30 mV. The cell mismatch correction circuitry is enabled by pulling the CB EN pin low, and disabled when CB EN is pulled to VDD or greater than 2.2 V.

If the internal cell balancing current of up to 15 mA is insufficient, the bq2920x may be configured via external circuitry to support much higher external cell balancing current.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### ORDERING INFORMATION

T <sub>A</sub>	PART NUMBER PACKAGE		PACKAGE	PACKAGE	OVP	ORDERING INFORMATION		
			DESIGNATOR	MARKING		TAPE AND REEL (LARGE)	TAPE AND REEL (SMALL)	
-40°C to	BQ29200	QFN-8	DRB	200	4.35 V	BQ29200DRBR	BQ29209DRBT	
+110°C	BQ29209			209	4.30 V	BQ29209DRBR	BQ29209DRBT	

#### THERMAL INFORMATION

		bq2920x	
	THERMAL METRIC <sup>(1)</sup>	DRB	UNITS
		8 PINS	
$\theta_{JA}$	Junction-to-ambient thermal resistance (2)	50.5	
$\theta_{\text{JC(top)}}$	Junction-to-case(top) thermal resistance (3)	25.1	
$\theta_{\sf JB}$	Junction-to-board thermal resistance (4)	19.3	9000
ΨЈТ	Junction-to-top characterization parameter (5)	0.7	°C/W
ΨЈВ	Junction-to-board characterization parameter (6)	18.9	
θ <sub>JC(bottom)</sub>	Junction-to-case(bottom) thermal resistance (7)	5.2	

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, ψ<sub>JT</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ<sub>JA</sub>, using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ<sub>JB</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ<sub>JA</sub>, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

#### **PIN FUNCTIONS**

PIN NAME	NO.	DESCRIPTION				
CB_EN	6	Cell balance enable				
CD	4	ection to external capacitor for programmable delay time				
GND	5	Ground pin				
OUT	8	ut				
VC1	2	Sense voltage input for bottom cell				
VC1_CB	3	Cell balance input for bottom cell				
VC2	1	Sense voltage input for top cell				
VDD	7	Power supply				

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#### **FUNCTIONAL BLOCK DIAGRAM**

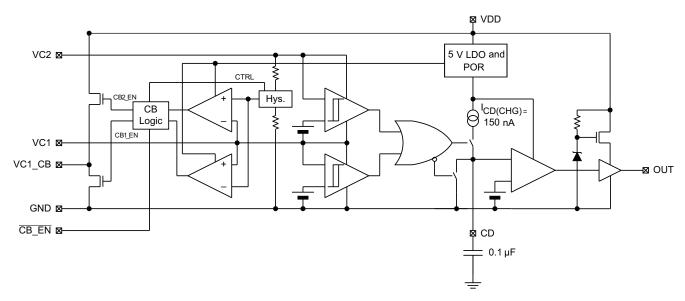


Figure 1. Block Diagram

### **ABSOLUTE MAXIMUM RATINGS**

Over-operating free-air temperature range (unless otherwise noted)(1)

	•	VALUE/UNIT		
Supply voltage range, V <sub>MAX</sub>	VDD-GND	–0.3 V to 16 V		
	VC2-GND, VC1-GND	–0.3 V to 16 V		
nput voltage range, V <sub>IN</sub>	VC2-VC1, CD-GND	–0.3 V to 8 V		
	CB_EN-GND	–0.3 V to 16 V		
Output voltage range, V <sub>OUT</sub>	OUT-GND	–0.3 V to 16 V		
Continuous total power dissipatio	n, P <sub>TOT</sub>	See package dissipation rating		
Storage temperature range, T <sub>STG</sub>		−65°C to 150°C		
Lead temperature (soldering, 10 s	s), T <sub>SOLDER</sub>	300°C		

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute—maximum—rated conditions for extended periods may affect device reliability.

# **RECOMMENDED OPERATING CONDITIONS**

		MIN	NOM	MAX	UNIT
Supply voltage, VDD		4		10	V
Input voltage range	VC2-VC1, VC1-GND	0		5	V
Delay time capacitance, t <sub>d(CD)</sub>	C <sub>CD</sub> (See Figure 8.)		0.1		μF
Voltage monitor filter resistance	R <sub>IN</sub> (See Figure 8.)	100	1K		Ω
Voltage monitor filter capacitance	C <sub>IN</sub> (See Figure 8.)	0.01	0.1		μF
Supply voltage filter resistance	R <sub>VD</sub> (See Figure 8.)		100	1K	Ω
Supply voltage filter capacitance	C <sub>VD</sub> (See Figure 8.)		0.1		μF
Cell balance resistance	R <sub>CB</sub> (See Figure 8 and PROTECTION (OUT) TIMING.)	100		4.7K	Ω
Operating ambient temperature ra	nge, T <sub>A</sub>	-40		110	°C

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# **ELECTRICAL CHARACTERISTICS**

Typical values stated where  $T_A = 25^{\circ}$ C and VDD = 7.2 V. Min/Max values stated where  $T_A = -40^{\circ}$ C to 110 °C and VDD = 4 V to 10 V (unless otherwise noted)

F	PARAMETER	T	TEST CONDITION	MIN	NOM	MAX	UNIT
	Overvoltage	bq29209			4.30		.,
V <sub>PROTECT</sub>	detection voltage	bq29200			4.35		V
V <sub>HYS</sub>	Overvoltage hysteresis	detection		200	300	400	mV
V <sub>OA</sub>	Overvoltage accuracy	detection	T <sub>A</sub> = 25°C	-10		10	mV
\ /	Overvoltage	threshold	$T_A = 0$ °C to $60$ °C	-0.4		0.4	m\/0/C
V <sub>OA_DRIFT</sub>	temperature	drift	$T_A = -40^{\circ}C \text{ to } 110^{\circ}C$	-0.6		0.6	mV°/C
<b>~</b>	Overvoltage	delay time	$T_A = 0$ °C to 60°C Note: Does not include external capacitor variation.	6.0	9.0	12.0	o/uE
ADELAY	DELAY scale factor		T <sub>A</sub> = -40°C to 110°C Note: Does not include external capacitor variation.	5.5	9.0	13.5	s/µF
X <sub>DELAY_CTM</sub> <sup>(1)</sup>	Overvoltage scale factor i Test Mode				0.08		s/µF
I <sub>CD(CHG)</sub>	Overvoltage charging curr				150		nA
I <sub>CD(DSG)</sub>	Overvoltage discharging of				60		μΑ
$V_{CD}$	Overvoltage external capa comparator t	acitor			1.2		V
I <sub>cc</sub>	Supply curre	nt	(VC2-VC1) = (VC1-GND) = 3.5 V (See Figure 4.)		3.0	6.0	μA
			(VC2-VC1) or (VC1-GND) > V <sub>PROTECT</sub> , VDD = 10 V, I <sub>OH</sub> = 0	6	8.25	9.5	V
			(VC2–VC1) or (VC1–GND) = $V_{PROTECT}$ , VDD = $V_{PROTECT}$ , $I_{OH}$ = -100 $\mu$ A, $I_{A}$ = 0°C to 60°C	1.75	2.5		V
V <sub>OUT</sub>	OUT pin driv	e voltage	(VC2–VC1) and (VC1–GND) < $V_{PROTECT}$ , $I_{OL}$ = 100 $\mu A, T_A$ = 25°C			200	mV
			(VC2–VC1) and (VC1–GND) < $V_{PROTECT}$ , $I_{OL}=0~\mu A,~T_{A}=25^{\circ}C$		0	10	mV
			VC2 = VC1 = VDD = 4 V, I <sub>OL</sub> = 100 μA			200	mV
I <sub>OH</sub>	High-level ou	itput current	OUT = 1.75 V, (VC2–VC1) or (VC1–GND) = $V_{PROTECT}$ , VDD = $V_{PROTECT}$ to 10 V, $T_A$ = 0°C to 60°C	-100			μΑ
I <sub>OL</sub>	Low-level ou	tput current	OUT = 0.05 V, (VC2–VC1) or (VC1–GND) $<$ V <sub>PROTECT</sub> , VDD = V <sub>PROTECT</sub> to 10 V, T <sub>A</sub> = 0°C to 60°C	30		85	μΑ
I <sub>OH_ZV</sub>	High-level sh output currer		OUT = 0 V, (VC2-VC1) = (VC1-GND) = V <sub>PROTECT</sub> VDD = 4 to 10 V			-8.0	mA
I	Input current	at VCv nine	Measured at VC1, (VC2–VC1) = (VC1–GND) = $3.5 \text{ V}$ , $T_A = 0^{\circ}\text{C}$ to $60^{\circ}\text{C}$ (See Figure 4.)	-0.2		0.2	μΑ
l <sub>IN</sub>	mput current	ut vox pins	Measured at VC2, (VC2–VC1) = (VC1–GND) = $3.5 \text{ V}$ , $T_A = 0^{\circ}\text{C}$ to $60^{\circ}\text{C}$ (See Figure 4.)			2.5	μΑ
V <sub>MM_DET_ON</sub>	Cell mismato threshold for		(VC2–VC1) versus (VC1–GND) and vice-versa when cell balancing is enabled. VC2 = VDD = 7.6 V	17	30	45	mV
V <sub>MM_DET_OFF</sub>	Cell mismato threshold for		Delta between (VC2–VC1) and (VC1–GND) when cell balancing is disabled. VC2 = VDD = 7.6 V	-9	0	9	mV
V <sub>CB_EN_ON</sub>	Cell balance threshold	enable ON	Active LOW pin at CB_EN			1	V
V <sub>CB_EN_OFF</sub>	Cell balance threshold	enable OFF	Active HIGH at CB_EN	2.2			V
I <sub>CB_EN</sub>	Cell balance input current		<del>CB_EN</del> = GND (See Figure 5.)			0.2	μΑ

<sup>(1)</sup> Specified by design. Not 100% tested in production.



# RECOMMENDED CELL BALANCING CONFIGURATIONS

Typical values stated where  $T_A$  = 25°C and (VC2–VC1), (VC1–GND) = 3.8 V. Min/Max values stated where  $T_A$  = -40°C to 110°C, VDD = 4 V to 10 V, and (VC2–VC1), (VC1–GND) = 3.0 V to 4.2 V. All values assume recommended supply voltage filter resistance  $R_{VD}$  of 100  $\Omega$  and 5% accurate or better cell balance resistor  $R_{CB}$ .

	PARAMETER	TEST CONDITION	MIN	NOM	MAX	UNIT
		$R_{CB} = 4700 \Omega$	0.5	0.75	1	
		R <sub>CB</sub> = 2200 Ω	1	1.5	2	
		$R_{CB} = 910 \Omega$	2	3	4	
I <sub>CB</sub>	Cell balance input current	$R_{CB} = 560 \Omega$	3	4.5	6	mA
		$R_{CB} = 360 \Omega$	3.5	6	8.5	
		$R_{CB} = 240 \Omega$	4	7.5	11	
		$R_{CB} = 120 \Omega$	5	10	15	

The cell balancing current may be calculated as follows:

Cell 1 (VC1-GND):

$$I_{CB1} = \frac{VC1}{R_{CB}}$$

Cell 2 (VC2-VC1):

$$I_{CB2} = \frac{(VC2 - VC1)}{(R_{CB} + R_{VD})}$$

### TYPICAL CHARACTERISTICS

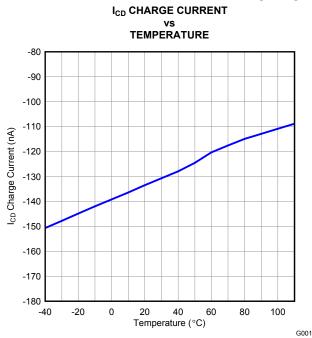


Figure 2. I<sub>CD</sub> Charge Current

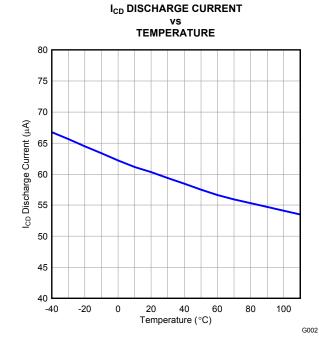


Figure 3. I<sub>CD</sub> Discharge Current

#### **TEST CONDITIONS**

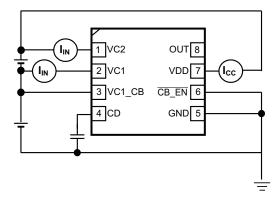


Figure 4. I<sub>CC</sub>, I<sub>IN</sub> Measurement

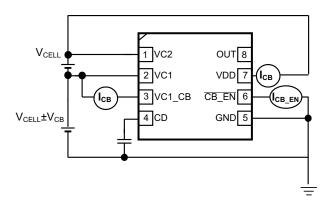


Figure 5. I<sub>CB</sub> Measurement

### PROTECTION (OUT) TIMING

Sizing the external capacitor is based on the desired delay time as follows:

$$C_{CD} = \frac{t_d}{X_{DELAY}}$$

Where  $t_d$  is the desired delay time and  $X_{DELAY}$  is the overvoltage delay time scale factor, expressed in seconds per microFarad.  $X_{DELAY}$  is nominally 9.0 s/ $\mu$ F. For example, if a nominal delay of 3 seconds is desired, use a  $C_{CD}$  capacitor that is 3 s / 9.0 s/ $\mu$ F = 0.33  $\mu$ F.

The delay time is calculated as follows:

$$t_d = C_{CD} \times X_{DFLAY}$$

If the cell overvoltage condition is removed before the external capacitor reaches the reference voltage, the internal current source is disabled and an internal discharge block is employed to discharge the external capacitor down to 0 V. In this instance, the OUT pin remains in a low state.

# Cell Voltage > V<sub>PROTECT</sub>

When one or both of the cell voltages rises above  $V_{PROTECT}$ , the internal comparator is tripped, and the delay begins to count to  $t_d$ . If the input remains above  $V_{PROTECT}$  for the duration of  $t_d$ , the bq2920x output changes from a low to a high state, by means of an internal pull-up network, to a regulated voltage of no more than 9.5 V when  $I_{OH} = 0$  mA.

The external delay capacitor should charge up to no more than the internal LDO voltage (approximately 5 V typically), and will fully discharge in approximately under 100 ms when the overvoltage condition is removed.



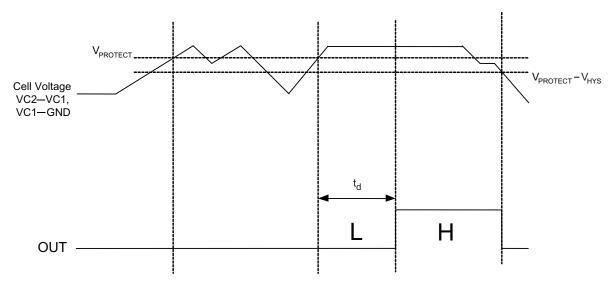


Figure 6. Timing for Overvoltage Sensing

### **CELL CONNECTION SEQUENCE**

#### **NOTE**

Before connecting the cells, propagate the overvoltage delay timing capacitor, C<sub>CD</sub>.

The recommended cell connection sequence begins from the bottom of the stack, as follows:

- 1. GND
- 2. VC1
- 3. VC2

While not advised, connecting the cells in a sequence other than that described above does not result in errant activity on the OUT pin. For example:

- 1. GND
- 2. VC2 or VC1
- 3. Remaining VCx pin

# **CELL BALANCE ENABLE CONTROL**

To avoid prematurely discharging the cells, it is recommended to turn off (pull high) the active-low Cell Balance Enable Control pin at lower State of Charge (SOC) levels.

### **CELL IMBALANCE AUTO-DETECTION (VIA CELL VOLTAGE)**

The  $V_{MM\_DET\_ON}$  and  $V_{MM\_DET\_OFF}$  specifications are calibrated where VDD = VC2 = 7.6 V and VC1 = 3.8 V. The recommended range of cell balancing is VC2 and VDD between 6.0 V and 8.4 V, and VC1 between 3.0 V and 4.2 V. Below VDD = 6.0 V, it is recommended to pull CB\_EN high to disable the cell balancing function.

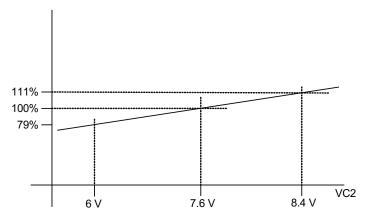


Figure 7.  $V_{MM\_DET\_ON}$  and  $V_{MM\_DET\_OFF}$  Threshold

### **BATTERY CONNECTION**

Figure 8 shows the configuration for the 2-series cell battery connection.

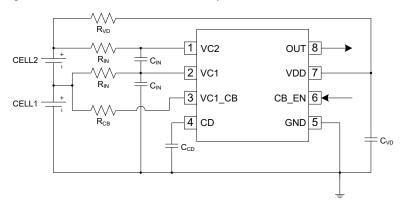


Figure 8. 2-Series Cell Configuration

### **EXTERNAL CELL BALANCING**

Higher cell balancing currents can be supported by means of a simple external network, as shown in Figure 9.

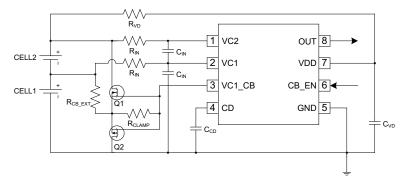


Figure 9. External Cell Balancing Configuration

 $R_{CLAMP}$  ensures that both Q1 and Q2 remain off when balancing is disabled, and should be sized above 2 k $\Omega$  to prevent excessive internal device current when the balancing network is activated.  $R_{CB\_EXT}$  determines the value of the balancing current, and is dependent on the voltage of the balanced cell, as follows:



$$I_{bal} = \frac{V_{CELL}}{R_{CB\_EXT}}$$

### **CUSTOMER TEST MODE**

Customer Test Mode (CTM) helps to greatly reduce the overvoltage detection delay time and enable quicker customer production testing. This mode is intended for quick-pass board-level verification tests, and, as such, individual cell overvoltage levels may deviate slightly from the specifications ( $V_{PROTECT}$ ,  $V_{OA}$ ). If accurate overvoltage thresholds are to be tested, use the standard delay settings that are intended for normal use.

To enter CTM, VDD should be set to approximately 9.5 V higher than VC2. When CTM is entered, the device switches from the normal overvoltage delay time scale factor,  $X_{DELAY}$ , to a significantly reduced factor of approximately 0.08, thereby reducing the delay time during an overvoltage condition.

#### **CAUTION**

Avoid exceeding any Absolute Maximum Voltages on any pins when placing the part into CTM. Also, avoid exceeding Absolute Maximum Voltages for the individual cell voltages (VC1–GND) and (VC2–VC1). Stressing the pins beyond the rated limits may cause permanent damage to the device.

To exit CTM, power off the device and then power it back on.

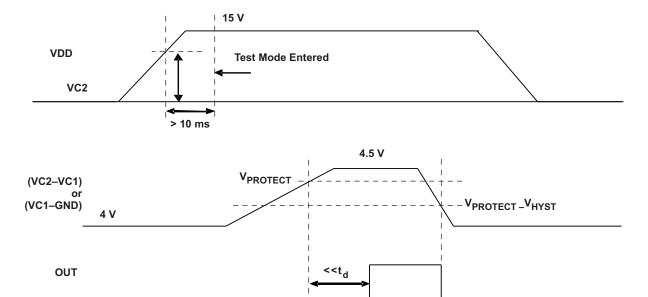


Figure 10. Voltage Test Limits



# **REVISION HISTORY**

С	Changes from Original (June 2010) to Revision A	Page
•	Changed values in X <sub>DELAY</sub> and X <sub>DELAY_CTM</sub> electrical characteristics	4
•	Changed specifications for V <sub>OUT</sub>	4
•	Changed test conditions for V <sub>OUT</sub> , I <sub>OH</sub> , and I <sub>OL</sub>	4
•	Added V <sub>MM_DET_ON</sub> : VC2 = VDD = 7.6 V	4
•	Changed V <sub>MM_DET_OFF</sub> : From VDD – VC2 – 7.6 V to VC2 = VDD = 7.6 V	4
•	Changed content in Recommended Cell Balancing Configurations section	5
•	Added I <sub>CD</sub> Charge Current figure	
	Added I <sub>CD</sub> Discharge Current figure	
	Changed X <sub>DELAY</sub> from nominally 8.0 s/µF to nominally 9.0 s/µF	
•	Changed Timing for Overvoltage Sensing figure	6
•		
•	Added External Cell Balancing section	8
•	Changed VDD value in Customer Test Mode from 8.5 V to 9.5 V	
	Changed the Voltage Test Limits figure	



# PACKAGE OPTION ADDENDUM

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#### **PACKAGING INFORMATION**

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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
BQ29209DRBR	ACTIVE	SON	DRB	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	209	Samples
BQ29209DRBT	ACTIVE	SON	DRB	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	209	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): Ti's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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<sup>(4)</sup> Only one of markings shown within the brackets will appear on the physical device.

PACKAGE MATERIALS INFORMATION

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# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ29209DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
BQ29209DRBT	SON	DRB	8	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

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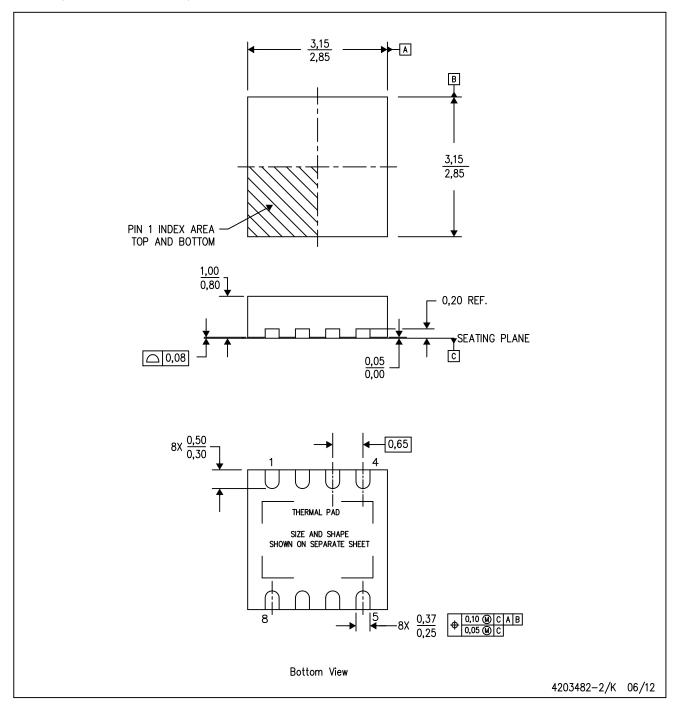


#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ29209DRBR	SON	DRB	8	3000	367.0	367.0	35.0
BQ29209DRBT	SON	DRB	8	250	210.0	185.0	35.0

DRB (S-PVSON-N8)

PLASTIC SMALL OUTLINE NO-LEAD



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Small Outline No-Lead (SON) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.



# DRB (S-PVSON-N8)

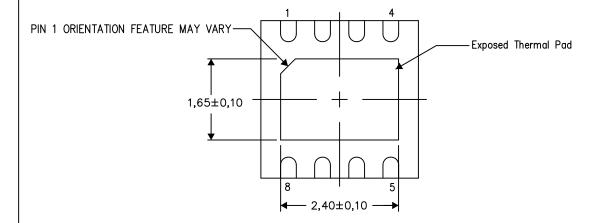
# PLASTIC SMALL OUTLINE NO-LEAD

### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

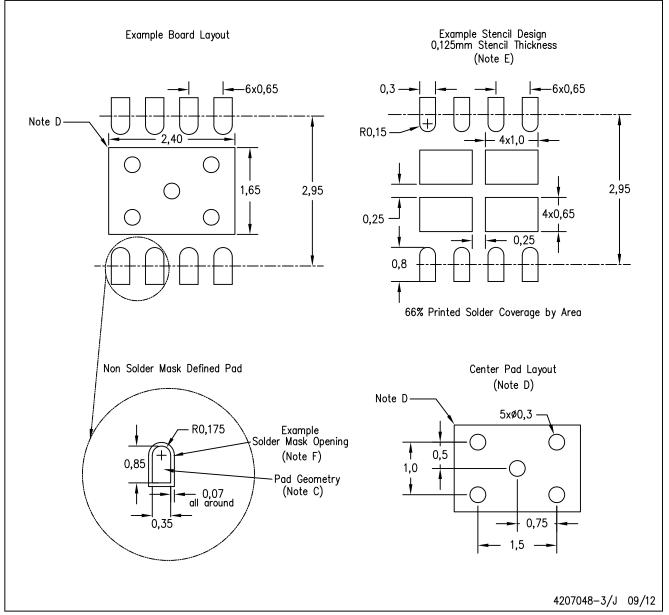
4206340-3/N 09/12

NOTE: All linear dimensions are in millimeters



# DRB (S-PVSON-N8)

# PLASTIC SMALL OUTLINE NO-LEAD



NOTES: A

- S: A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">https://www.ti.com</a>.
  - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
  - F. Customers should contact their board fabrication site for solder mask tolerances.



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